

SCHOTTKY RECTIFIER
HIGH EFFICIENCY SERIES

75LQ150
75 Amp, 150V

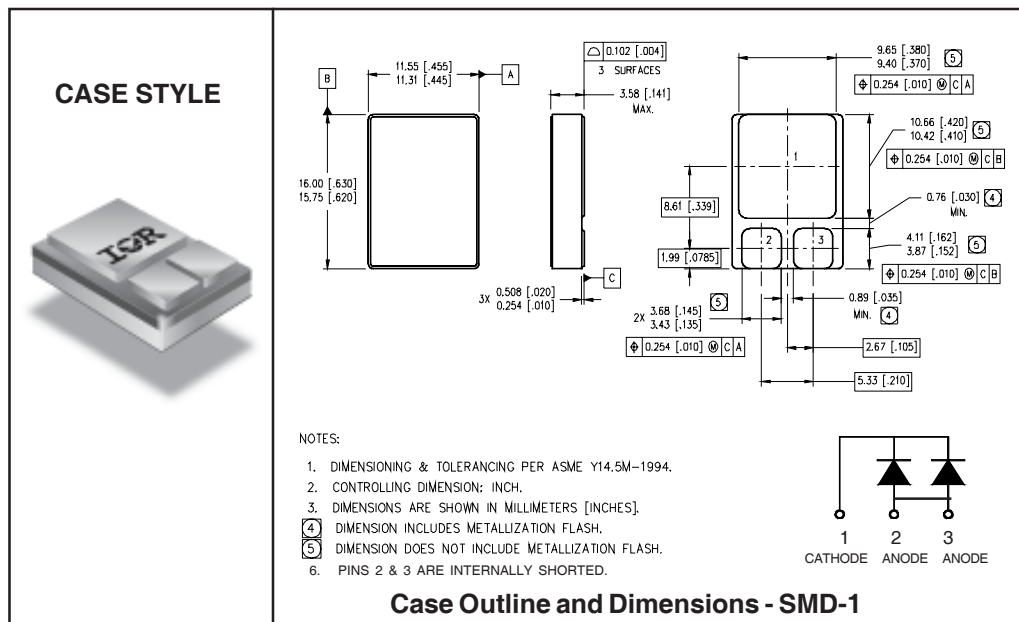
Major Ratings and Characteristics

Characteristics	75LQ150	Units
$I_{F(AV)}$	75	A
V_{RRM}	150	V
I_{FSM} @ $t_p = 8.3ms$ half-sine	700	A
V_F @ 75Apk, $T_J = 125^\circ C$	0.78	V
T_J, T_{stg} Operating and storage	-55 to 150	$^\circ C$

Description/Features

The 75LQ150 Schottky rectifier has been expressly designed to meet the rigorous requirements of HiRel environments. It is packaged in the hermetic surface mount SMD-1 ceramic package. The device's forward voltage drop and reverse leakage current are optimized for the lowest power loss and the highest circuit efficiency for typical high frequency switching power supplies and resonant power converters. Full MIL-PRF-19500 quality conformance testing is available on source control drawings to TX, TXV and S quality levels.

- Hermetically Sealed
- Low Forward Voltage Drop
- High Frequency Operation
- Guard Ring for Enhanced Ruggedness and Long term Reliability
- Surface Mount
- Lightweight



Voltage Ratings

Part number	75LQ150
V _R Max. DC Reverse Voltage (V)	150
V _{RWM} Max. Working Peak Reverse Voltage (V)	

Absolute Maximum Ratings

Parameters	Limits	Units	Conditions
I _{F(AV)} Max. Average Forward Current See Fig. 5	75	A	50% duty cycle @ T _C = 95°C, square waveform ②
I _{FSM} Max. Peak One Cycle Non - Repetitive Surge Current	700	A	@ t _p = 8.3 ms half-sine ②

Electrical Specifications

Parameters	Limits	Units	Conditions
V _{FM} Max. Forward Voltage Drop See Fig. 1 ①	1.18	V	@75A T _J = -55°C
	1.45	V	@150A
	1.06	V	@75A T _J = 25°C
	1.44	V	@150A
	0.78	V	@75A T _J = 125°C
	0.96	V	@150A
I _{RM} Max. Reverse Leakage Current See Fig. 2 ①	0.2	mA	T _J = 25°C V _R = rated V _R
	32	mA	T _J = 125°C
C _T Max. Junction Capacitance	1600	pF	V _R = 5V _{DC} (1MHz, 25°C)
L _S Typical Series Inductance	5.9	nH	Measured from center of cathode pad to center of anode pad

Thermal-Mechanical Specifications

Parameters	Limits	Units	Conditions
T _J Max. Junction Temperature Range	-55 to 150	°C	
T _{stg} Max. Storage Temperature Range	-55 to 150	°C	
R _{thJC} Max. Thermal Resistance, Junction to Case	0.75	°C/W	DC operation See Fig. 4 ②
wt Weight (Typical)	2.6	g	
Die Size (Typical)	(2)158 X158	mils	
Case Style	SMD-1		

① Pulse Width < 300μs, Duty Cycle < 2%

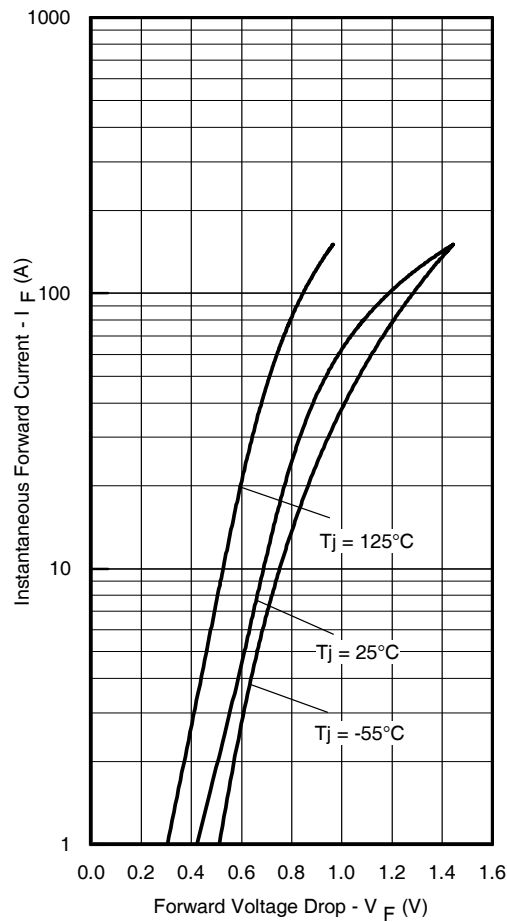


Fig. 1 - Max. Forward Voltage Drop Characteristics

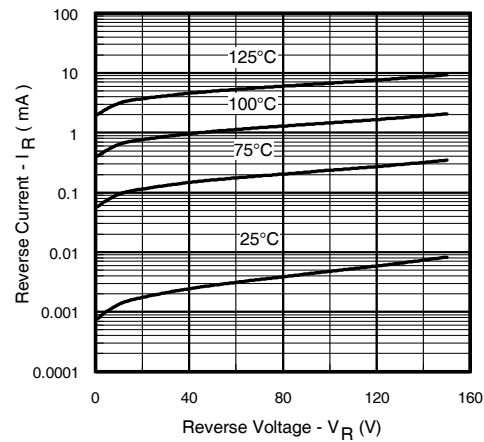


Fig. 2 - Typical Values of Reverse Current Vs. Reverse Voltage

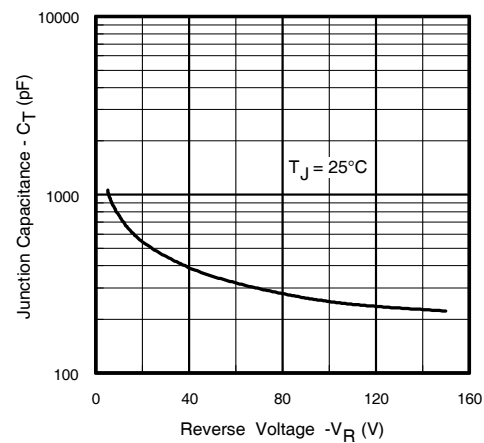
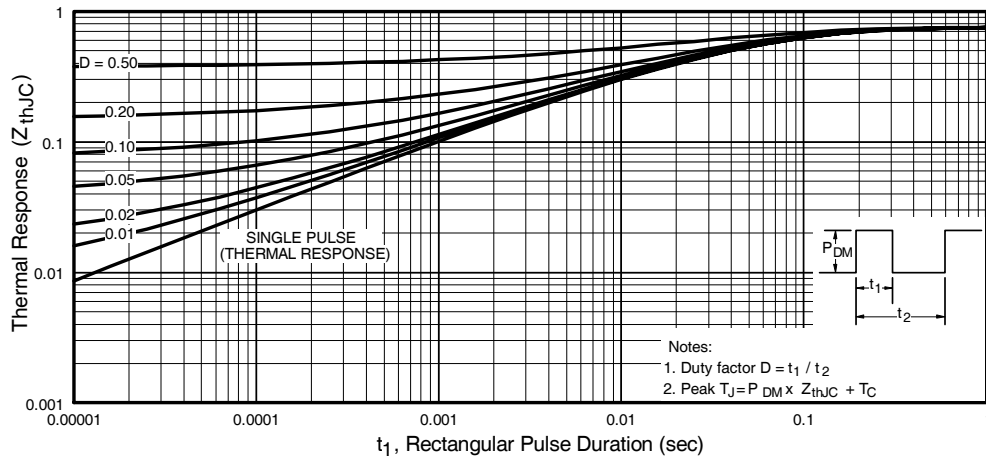
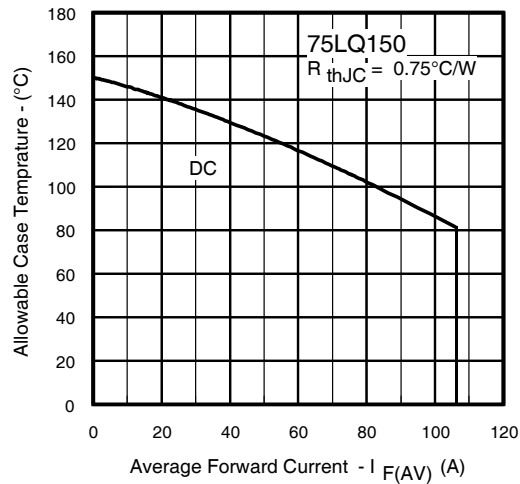


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage

Fig. 4 - Max. Thermal Impedance Z_{thJC} CharacteristicsFig. 5 - Max. Allowable Case Temperature Vs.
Average Forward Current